



# Precision, Rail to Rail Input and Output, Quad Operational Amplifier

## OP484

### 1.0 SCOPE

This specification documents the detailed requirements for Analog Devices space qualified die including die qualification as described for Class K in MIL-PRF-38534, Appendix C, Table C-II except as modified herein.

The manufacturing flow described in the STANDARD DIE PRODUCTS PROGRAM brochure at <http://www.analog.com/aerospace> is to be considered a part of this specification.

This data sheet specifically details the space grade version of this product. A more detailed operational description and a complete data sheet for commercial product grades can be found at [www.analog.com/OP484](http://www.analog.com/OP484)

### 2.0 Part Number. The complete part number(s) of this specification follow:

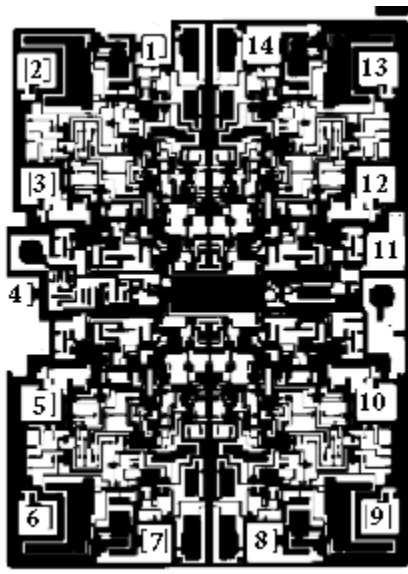
Part Number	Description
OP484-000C	Precision, Rail to Rail Input and Output, Quad Operational Amplifier
OP484R000C	Radiation Tested, Precision, Rail to Rail Input and Output, Quad Operational Amplifier

### 3.0 Die Information

#### 3.1 Die Dimensions

Die Size	Die Thickness	Bond Pad Metalization
80 mil x 110 mil	19 mil ± 2 mil	Al/Cu

#### 3.2 Die Picture



1. OUTPUT A
2. -INPUT A
3. +INPUT A
4. +Vs
5. +INPUT B
6. -INPUT B
7. OUTPUT B
8. OUTPUT C
9. -INPUT C
10. +INPUT C
11. -Vs
12. +INPUT D
13. -INPUT D
14. OUTPUT D

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Rev. G

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# OP484

## 3.3 Absolute Maximum Ratings <sup>1/</sup>

Supply Voltage .....	±18V
Differential Input Voltage .....	±0.6V
Input Voltage .....	±18V
Output Short Circuit Duration .....	Indefinite
Storage Temperature Range .....	-65°C to +150°C
Operating Temperature Range .....	-55°C to +125°C
Junction Temperature (T <sub>J</sub> ).....	+150°C

Absolute Maximum Ratings Notes:

- <sup>1/</sup> Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

## 4.0 Die Qualification

In accordance with class-K version of MIL-PRF-38534, Appendix C, Table C-II, except as modified herein.

- (a) Qual Sample Size and Qual Acceptance Criteria – 10/0
- (b) Qual Sample Package – DIP
- (c) Pre-screen electrical test over temperature performed post-assembly prior to die qualification.

**Table I - Dice Electrical Characteristics**

Parameter	Symbol	Conditions <sup>1/</sup>	Limit Min	Limit Max	Units
$V_S = +5V, V_{CM} = 2.5V$					
Input Offset Voltage	V <sub>OS</sub>			200	μV
Input Offset Current	I <sub>OS</sub>	<u>2/</u>		50	nA
Input Bias Current	I <sub>B</sub>	<u>2/</u>		350	nA
Input Voltage Range	IVR		1	4	V
Common Mode Rejection Ratio	CMRR	V <sub>CM</sub> = IVR	86		dB
Output High Voltage	V <sub>OH</sub>	I <sub>L</sub> = 1mA	4.85		V
Output Low Voltage	V <sub>OL</sub>	I <sub>L</sub> = 1mA		125	mV
Large Signal Voltage Gain	A <sub>VO</sub>	R <sub>L</sub> ≥ 2kΩ V <sub>OUT</sub> = 1V to 4V	50		V/mV
Supply Current <sup>3/</sup>	I <sub>SY</sub>	V <sub>OUT</sub> = 2.5V		5.8	mA
$V_S = \pm 15V, V_{CM} = 0V$					
Input Offset Voltage	V <sub>OS</sub>			150	μV
Input Offset Current	I <sub>OS</sub>			50	nA
Input Bias Current	I <sub>B</sub>			350	nA

Table I - Dice Electrical Characteristics (Continued)

Parameter	Symbol	Conditions <u>1/</u>	Limit Min	Limit Max	Units
$V_S = \pm 15V, V_{CM} = 0V$					
Input Voltage Range	IVR		-15	+15	
Common Mode Rejection Ratio	CMRR	$V_{CM} = IVR$	80		dB
Power Supply Rejection Ratio	PSRR	$V_S = \pm 2V$ to $\pm 18V$	90		dB
Large Signal Voltage Gain	$A_{vo}$	$R_L \geq 2k\Omega$ $V_{OUT} = \pm 10V$	150		V/mV
Supply Current <u>2/</u>	$I_{SY}$	$V_{OUT} = 0V$		8	mA

Table I Notes:

- 1/  $T_A = 25^\circ C$ , unless otherwise specified.
- 2/ Guaranteed by  $V_S = \pm 15V$  test.
- 3/  $I_{SY}$  limit = total all four amplifiers.

**Table II - Electrical Characteristics for Qual Samples**

Parameter	Symbol	Conditions	Sub-groups	Limit Min	Limit Max	Units
<b><math>V_S = +5V, V_{CM} = 2.5V</math></b>						
Input Offset Voltage	$V_{OS}$		1		200	$\mu V$
			2, 3		400	
			M, D, L, R <u>3/</u>	1	600	
Input Offset Current	$I_{OS}$	<u>1/</u>	1, 2, 3		50	nA
			M, D, L, R <u>3/</u>	1	400	
Input Bias Current	$I_B$	<u>1/</u>	1		350	
			2, 3		575	
			M, D, L, R <u>3/</u>	1	3000	
Common Mode Rejection Ratio <u>4/</u>	CMRR	$V_{CM} = 1V$ to $4V$	1, 2, 3	86		dB
Output High Voltage <u>4/</u>	$V_{OH}$	$I_L = 1mA$	4	4.85		V
Output Low Voltage <u>4/</u>	$V_{OL}$	$I_L = 1mA$	4		125	mV
Large Signal Voltage Gain	$A_{VO}$	$R_L \geq 2k\Omega$ $V_{OUT} = 1V$ to $4V$	4	50		V/mV
			5, 6	25		
			$R_L \geq 10k\Omega$ $V_{OUT} = 1V$ to $4V$	M, D, L, R <u>3/</u>	4	
Supply Current <u>2/</u>	$I_{SY}$	$V_{OUT} = 2.5V$	1		5.8	mA
			M, D, L, R <u>3/</u>	1	5.85	
<b><math>V_S = \pm 15V, V_{CM} = 0V</math></b>						
Input Offset Voltage <u>4/</u>	$V_{OS}$		1		250	$\mu V$
			2, 3		500	
Average Input Offset Voltage Drift <u>4/</u>	$TCV_{OS}$		8		2	$\mu V/^\circ C$
Input Offset Current <u>4/</u>	$I_{OS}$		1, 2, 3		50	nA
Input Bias Current <u>4/</u>	$I_B$		1		350	nA
			2, 3		575	
Common Mode Rejection Ratio <u>4/</u>	CMRR	$V_{CM} = -15V$ to $+15V$	1, 2, 3	80		dB
Power Supply Rejection Ratio <u>4/</u>	PSRR	$V_S = \pm 2V$ to $\pm 18V$	1, 2, 3	90		dB
Large Signal Voltage Gain <u>4/</u>	$A_{VO}$	$R_L \geq 2k\Omega$ $V_{OUT} = \pm 10V$	4	150		V/mV
			5, 6	75		
Supply Current <u>2/</u> <u>4/</u>	$I_{SY}$	$V_{OUT} = 0V$ $V_S = \pm 18V, V_{OUT} = 0V$	1		8	mA
			1, 2, 3		9	

Table II Notes:

- 1/ Guaranteed by  $V_S = \pm 15V$  test.
- 2/ limit = total all four amplifiers.
- 3/  $I_{SY}$  Devices tested at 100Krad irradiation.
- 4/ Parameter not tested post irradiation.

**Table III - Life Test Endpoint and Delta Parameter**  
 (Product is tested in accordance with Table II with the following exceptions)

Parameter	Symbol	Sub-groups	Burn In Limit Min	Burn In Limit Max	Life Test Limit Min	Life Test Limit Max	Life Test Delta	Units
Input Offset Voltage $V_S = \pm 15V$	$V_{OS}$	1		500		750	$\pm 250$	$\mu V$
		2, 3				1000		
Input Bias Current $V_S = \pm 15V$	$I_B$	1		450		550	$\pm 100$	nA
		2, 3				775		
Input Offset Current $V_S = \pm 15V$	$I_{OS}$	1		60		100	$\pm 40$	nA
		2, 3				100		
Input Offset Voltage $V_S = +5V$	$V_{OS}$	1		300		450		$\mu V$
		2, 3				650		

**5.0 Life Test/Burn-In Information**

- 5.1 HTRB is not applicable for this drawing.
- 5.2 Burn-in is per MIL-STD-883 Method 1015 test condition B or C.
- 5.3 Steady state life test is per MIL-STD-883 Method 1005.

Rev	Description of Change	Date
A	Initiate	4-Nov-111
B	Update web address	Jan. 25, 2002
C	Add radiation part number. Update web address	Feb. 10, 2003
D	Update header/footer and add to 1.0 scope description.	March 5, 2008
E	Add Junction Temperature ( $T_J$ ).....+150°C to 3.3-Absolute Max Ratings section & aligned/centered Table II	April 3, 2008
F	Updated Section 4.0c note to indicated pre-screen temp testing being performed.	June 5 2009
G	Updated fonts and size to ADI standards. Touched up die picture for clarity.	Oct 3, 2011